

M.2 (P80) 4IE3 Series Ultra iSLC

Customer:	
Customer	
Part Number:	
Innodisk	
Part Number:	
Innodisk	
Model Name:	
Date:	

Customer

Approver

Innodisk

Approver

Total Solution For Industrial Flash Storage



Features:

- PCIe Gen.4 x4, NVMe SSD
- Innodisk 3D TLC NAND
- M.2 Type 2280
- Standard/Wide-temperature
- iPowerguard
- iDataguard
- Dynamic Thermal Management
- 256 bit AES hardware based encryption
- Support Ultra iSLC technology
- Support Write Protection (optional)
- Support TCG OPAL function (optional)

Performance:

- Sequential Read up to 3,500 MB/s
- Sequential Write up to 3,200 MB/s

Power Requirements:

Input Voltage:	3.3V± 5%
Max Operating Wattage (R/W):	4.8W
Idle Wattage:	1.0W

Reliability:

Capacity	TBW	DWPD
40GB	1,925	28.9
80GB	3,849	28.9
160GB	8,174	30.7
320GB	16,683	31.4
640GB	36,505	34.3

Data Retention	10 Years
Warranty	5 Years

For warranty details, please refer to:

https://www.innodisk.com/en/support_and_service/warranty



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REVISION HISTORY

Revision	Description	Date
V1.0	First Release	Dec., 2023
V1.1	Revise TBW	Jan., 2024
V1.2	Revise PN rule	Feb., 2024
V1.3	Update Product Feature	Feb., 2024



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1. Product Overview

1.1 Introduction of Innodisk M.2 (P80) 4IE3

Innodisk M.2 (P80) 4IE3 is Ultra iSLC series which is designed to outdo the endurance, performance and reliability of 3D TLC-based solutions. Through the use of flash management algorithms, Ultra iSLC improves SSD endurance up to 100,000 times. In addition, Ultra iSLC improves the performance of solid state drives, with similar write performance of SLC-based solutions.

M.2 (P80) 4IE3 supports PCIe Gen. 4x4, and it is compliant with NVMe 1.4 providing excellent performance. M.2 (P80) 4IE3 with heat-spreading design dissipate heat generating from IC making SSD perform more steady. M.2 (P80) 4IE3 have Die RAID protection to reduce bad blocks happening and optimize data integrity.

Innodisk M.2 (P80) 4IE3 is designed with AES engine, which is a built in controller. When controller receives the data package from host, AES engine encrypts the data package and saves the encrypted data into NAND flash. Thus, unauthorized personal has no access to decrypt the data in NAND flash.

1.2 Product View and Models

Innodisk M.2 (P80) 4IE3 is available in follow capacities with industrial 3D TLC flash ICs.

M.2 (P80) 4IE3 40GB

M.2 (P80) 4IE3 80GB

M.2 (P80) 4IE3 160GB

M.2 (P80) 4IE3 320GB

M.2 (P80) 4IE3 640GB



Figure 1: Innodisk M.2 (P80) 4IE3 (Standard-temperature)



Figure 2: Innodisk M.2 (P80) 4IE3 (Wide-temperature)

(Note. For write protection function, please contact sales for customization)



1.3 PCIe Interface

Innodisk M.2 (P80) 4IE3 supports PCIe Gen.4 interface and compliant with NVMe 1.4. M.2 (P80) 4IE3 can work under PCIe Gen. 1, Gen. 2 and Gen. 3.

Most of operating system includes NVMe in-box driver now. For more information about the driver support in each OS, please visit https://nvmexpress.org/drivers/.



2. Product Specifications

2.1 Capacity and Device Parameters

M.2 (P80) 4IE3 device parameters are shown in Table 1.

Table 1: Device parameters

Capacity	Cylinders	Heads	Sectors	LBA	User Capacity(MB)
40GB				78161328	38164
80GB				156301488	76319
160GB	16383	16	63	312581808	152627
320GB				625142448	305245
640GB				1250263728	610480

2.2 Performance

Burst Transfer Rate: 8 GB/s

Table 2: Performance- 112 Layers 3D TLC

Capacity	Unit	40GB	80GB	160GB	320GB	640GB
Sequential*		1 450	2 000	2 500	2 500	2 500
Read (Q8T1)	MB/s	1,450	2,900	3,500	3,500	3,500
Sequential*		020	1.650	2.000	2.050	2 200
Write (Q8T1)		830	1,650	3,000	2,950	3,200
4KB Random**		45.000	06.000	355,000	222.000	FC1 000
Read (Q32T16)	IOPS	45,000	86,000	355,000	332,000	561,000
4KB Random**		106.000	360,000	627.000	627.000	625.000
Write (Q32T16)		196,000	369,000	637,000	627,000	625,000

Note: * Performance results are 4IE3 with Innodisk BiCS5 NAND composition measured in Room Temperature with Out-of-Box devices and may vary depending on overall system setup.

Note: ** Performance results are based on CrystalDiskMark 8.0.1 with file size 1000MB. Unit of 4KB item is IOPS.



2.3 Electrical Specifications

2.3.1 Power Requirement

Table 3: Innodisk M.2 (P80) 4IE3 Power Requirement

Item	Symbol Rating		Unit
Input voltage	V _{IN}	+3.3 DC +- 5%	<

2.3.2 Power Consumption

Table 4: Power Consumption

Mode	Power Consumption (W)
Read	4.8
Write	4.6
Idle	1.0
Power on peak	4.0

Target: 640GB M.2 (P80) 4IE3

Note: Current results may vary depending on system components and power circuit design. Please refer to the test report for other capacities.

2.4 Environmental Specifications

2.4.1 Temperature Ranges

Table 5: Temperature range for M.2 (P80) 4IE3

Temperature	Range
Operating	Standard Grade: 0°C to +70°C
	Industrial Grade: -40°C to +85°C
Storage	-40°C to +85°C

2.4.2 Humidity

Relative Humidity: 10-95%, non-condensing

2.4.3 Shock and Vibration

Table 6: Shock/Vibration Testing for M.2 (P80) 4IE3

Reliability	Test Conditions	Reference Standards
Vibration	7 Hz to 2K Hz, 20G, 3 axes	IEC 60068-2-6
Mechanical Shock	Duration: 0.5ms, 1500 G, 3 axes	IEC 60068-2-27

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2.4.4 Mean Time between Failures (MTBF)

Table 7 summarizes the MTBF prediction results for various M.2 (P80) 4IE3 configurations. The analysis was performed using a RAM Commander[™] failure rate prediction.

- **Failure Rate**: The total number of failures within an item population, divided by the total number of life units expended by that population, during a particular measurement interval under stated condition.
- **Mean Time between Failures (MTBF)**: A basic measure of reliability for repairable items: The mean number of life units during which all parts of the item perform within their specified limits, during a particular measurement interval under stated conditions.

Table 7: M.2 (P80) 4IE3 MTBF

Product	Condition	MTBF (Hours)	
Innodisk M.2 (P80) 4IE3	Telcordia SR-332 GB, 25°C	>3,000,000	

2.5 CE and FCC Compatibility

M.2 (P80) 4IE3 conforms to CE and FCC requirements.

Table 8: M.2 (P80) 4IE3 ESD

Reliability	Reference standards
Electrostatic Discharge (ESD)	EC 61000-4-2 ESD

2.6 RoHS Compliance

M.2 (P80) 4IE3 is fully compliant with RoHS directive.



2.7 Reliability

Table 9: M.2 (P80) 4IE3 TBW

Table 5. Ph.2 (P00) 4125 TBW				
Parameter	Valu	Value		
Read Cycles	Unlin	nited Read Cycles		
Flash endurance	100,0	000 P/E cycles		
Error Correct Code	Supp	ort(LDPC)		
Data Retention	Unde	r 40°C:		
	10 Ye	ears at Initial NAND Status;	1 Year at NAND Life End	
TBW* (Total Bytes W	ritten)	Unit: TB		
Capacity		Sequential workload	Client workload	
40GB		3,551	1,925	
80GB		7,102	3,849	
160GB		14,204	8,174	
320GB 28,409 16,683				
640GB 56,818 36,505				
* Note:				
1. Sequential: Mainly sequential write are estimated by PassMark Burnin Test v8.1 pro.				
2. Client: Follow JESD218 Test method and JESD219A Workload, tested by ULINK.				

2.8 Transfer Mode

M.2 (P80) 4IE3 support following transfer mode:

3. Based on out-of-box performance.

PCIe Gen. 4: 2 GB/s PCIe Gen. 3: 1 GB/s PCIe Gen. 2: 500 MB/s PCIe Gen. 1: 250 MB/s

2.9 Pin Assignment

Innodisk M.2 (P80) 4IE3 follows standard M.2 spec, socket 3 key M PCIe-based SSD pinout. See Table 10 for M.2 (P80) 4IE3 pin assignment.

Table 10: Innodisk M.2 (P80) 4IE3 Pin Assignment

Signal Name	Pin #	Pin #	Signal Name
		75	GND
3.3V	74	73	GND
3.3V	72	71	GND
3.3V	70	69	NC
NC	68	67	NC

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Notch	66	65	Notch
Notch	64	63	Notch
Notch	62	61	Notch
Notch	60	59	Notch
NC (Remark for MFG_CLOCK)	58	57	GND
NC (Remark for MFG_DATA)	56	55	REFCLKp
NC	54	53	REFCLKn
CLKREQ# (I/O) (0V/1.8V/3.3V)	52	51	GND
PERST# (I) (0V/1.8V/3.3V)	50	49	PERp0
NC	48	47	PERn0
NC	46	45	GND
ALERT# (I) (0/1.8V)	44	43	PETp0
SMB_DATA (I/O) (0/1.8V)	42	41	PETn0
SMB_CLK (I/O) (0/1.8V)	40	39	GND
NC	38	37	PERp1
NC	36	35	PERn1
NC	34	33	GND
NC	32	31	PETp1
NC	30	29	PETn1
NC	28	27	GND
NC	26	25	PERp2
NC	24	23	PERn2
NC	22	21	GND
NC	20	19	PETp2
3.3V	18	17	PETn2
3.3V	16	15	GND
3.3V	14	13	PERp3
3.3V	12	11	PERn3
LED1# (O) (OD)	10	9	GND
NC	8	7	PETp3
NC	6	5	PETn3
3.3V	4	3	GND
3.3V	2	1	GND



2.10 Mechanical Dimensions

M.2 Type 2280

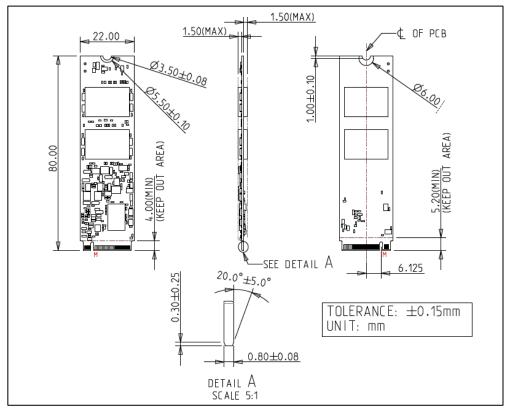


Figure 3: Innodisk M.2 (P80) 4IE3 mechanical drawing

M.2 Type 2280 with heatsink (Default accessory for WT)

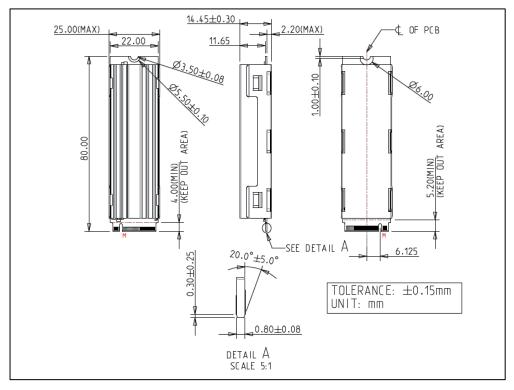


Figure 4: Innodisk M.2 (P80) 4IE3 with heatsink



2.11 Assembly Weight

An Innodisk M.2 (P80) 4IE3 within NAND flash ICs, 640GB's weight is 7 grams approximately.

2.12 Seek Time

Innodisk M.2 (P80) 4IE3 is not of magnetic rotating design. There is no seek or rotational latency.

2.13 NAND Flash Memory

Innodisk M.2 (P80) 4IE3 uses industrial 3D TLC NAND flash memory, which is non-volatility, high reliability and high speed memory storage.



3. Theory of Operation

3.1 Overview

Figure 5 shows the operation of Innodisk M.2 (P80) 4IE3 from the system level, including the major hardware blocks.

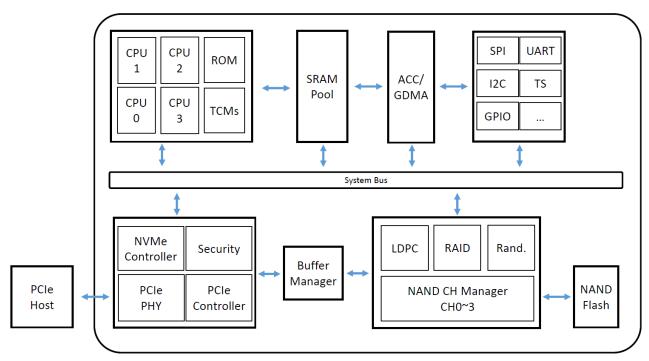


Figure 5: Innodisk M.2 (P80) 4IE3 Block Diagram

Innodisk M.2 (P80) 4IE3 integrates a PCIe Gen.4 x4 controller and NAND flash memories. Communication with the host occurs through the host interface, using the standard NVM Express protocol. Communication with the flash device(s) occurs through the flash interface.

3.2 PCIe Gen.4 x4 Controller

Innodisk M.2 (P80) 4IE3 is designed with innodisk ID309, a PCIe Gen.4 x4 controller which is compliant with NVMe 1.4, up to 64.0Gbps transfer speed. In addition, it is compliant with PCIe Gen. 1, Gen. 2 and Gen. 3 specification. The controller supports up to four channels for flash interface.

3.3 Error Detection and Correction

Innodisk M.2 (P80) 4IE3 is designed with hardware LDPC ECC engine with hard-decision and soft-decision decoding. Low-density parity-check (LDPC) codes have excellent error correcting performance close to the Shannon limit when decoded with the belief-propagation (BP) algorithm using soft-decision information.



3.4 Wear-Leveling

Flash memory can be erased with a limited number of cycles. This number is called the **erase cycle limit** or **write endurance limit** and is defined by the flash NAND vendor. The erase cycle limit applies to each individual erase block in the flash device.

Innodisk M.2 (P80) 4IE3 uses a combination of two types of wear leveling- dynamic and static wear leveling- to distribute write cycling across an SSD and balance erase count of each block, thereby extending device lifetime.

3.5 Bad Blocks Management

Bad Blocks are blocks that contain one or more invalid bits whose reliability are not guaranteed. The Bad Blocks may be presented while the SSD is shipped, or may develop during the lifetime of the SSD. When a Bad Block is detected, it will be flagged as unusable block by firmware. The SSD implement Bad Blocks management that consists of Bad Blocks replacement and Error Correcting to avoid data error occurred. The functions will be enabled automatically to transfer data from Bad Blocks to spare blocks, and correct error bit.

3.6 Garbage Collection/TRIM

Garbage collection and TRIM technology are used to maintain data consistency and perform continual data cleansing on SSDs. It runs as a background process, freeing up valuable controller resources while sorting good data into available blocks, and deleting bad blocks. It also significantly reduces write operations to the drive, thereby increasing the SSD's speed and lifespan.

3.7 End to End Data Path Protection

End-to-end Data Path Protection that secures the data transmission between host system and NAND Flash. In the transmission path, no matter in or out, all buffer and storage implement Error Code Correction that optimizes the data integrity in the whole transmission of SSD.

3.8 Thermal Management

M.2 (P80) 4IE3 has built-in thermal sensor which can detect environment temperature of SSD. In the meantime, firmware will monitor the thermal sensor to prevent any failure of overheating. During extreme temperature, firmware will adjust the data transfer behavior to maintain the SSD's reliable operation.

3.9 iDataGuard

Innodisk's iData Guard is a comprehensive data protection mechanism that functions before and after a sudden power outage to the SSD. Low-power detection terminates data writing before an abnormal power-off, while table-remapping after power-on deletes corrupt data and maintains data integrity. Innodisk's iData Guard provides effective power cycling management, preventing data stored in flash from degrading with use.



3.10 Thermal Throttling

Thermal throttling is a protective mechanism designed to safeguard components from potential damage caused by excessive temperatures. When an SSD approaches a critical temperature threshold, Innodisk firmware activates the thermal throttling mechanism to regulate the SSD's temperature. Thermal throttling is crucial for SSDs since it prevents drive damage, which could otherwise result in data loss. However, it's worth noting that when thermal throttling is activated, read and write tasks may experience a reduction in speed.

3.11 TCG OPAL (Optional)

OPAL is a set of specifications for features of data storage devices that enhance security. These specifications are published by the Trusted Computing Group's Storage Work Group. Innodisk 4IE3 is compliant with TCG OPAL 2.0(*1). The capability of TCG OPAL Security mode allows multiple users with independent access control to read/write/erase independent data areas (LBA ranges). Each locking range adjusts by authenticated authority. Note that by default there is a single "Global Range" that encompasses the whole user data area. In TCG Opal Security Mode, Revert, Revert SP and GenKey command can erase all of data including global range and locking range; in the meantime generate the new encrypted key.

*1. You need to install TCG OPAL software to implement OPAL function, which is supplied by TCG OPAL software developed company



4. Installation Requirements

4.1 M.2 (P80) 4IE3 Pin Directions

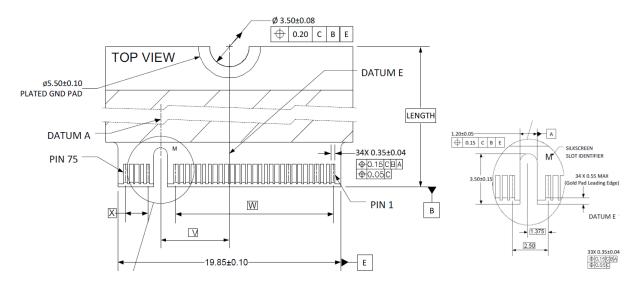


Figure 6: Signal Segment and Power Segment

4.2 Electrical Connections for M.2 (P80) 4IE3

M.2 interconnect is based on a 75 position Edge Card connector. The 75 position connector is intended to be keyed so as to distinguish between families of host interfaces and the various Sockets used in general Platforms. M.2 (P80) 4IE3 is compliant with M.2 Socket 3 key M.

4.3 Device Drive

M.2 (P80) 4IE3 is compliant with NVMe 1.4. Both Operation System and BIOS should include NVMe driver to compatible with NVMe device. Nowadays, most of OS includes NVMe in-box driver now. For more information about the driver support in each OS, please visit the website https://nvmexpress.org/drivers/. For BIOS NVMe driver support please contact with motherboard manufacturers.



5. SMART / Health Information

This log page is used to provide SMART and general health information. The information provided is over the life of the controller and is retained across power cycles. More details about Set Features command; please refer to NVM Express 1.4

5.1 Get Log Page (Log Identifier 02h)

Innodisk 4IE3 series SMART / Health Information Log are listed in following table.

Table 11: Get Log Page - SMART / Health Information Log

/tes	Description				
	Critical Warning: This field indicates critical warnings for the state of the controller. I				
	corresponds	s to a critical warning type; multiple bits may be set to `1'. If a bit is cleared to `0			
	then that cr	itical warning does not apply. Critical warnings may result in an asynchronous eve			
	notification	to the host. Bits in this field represent the state at the time the Get Log Part			
	command is	s processed and may not reflect the state at the time a related asynchronous eve			
	notification,	, if any, occurs or occurred.			
	Bit	Definition			
	0	If set to '1', then the available spare capacity has fallen below the			
		threshold.			
	1	If set to `1', then a temperature is:			
		a) greater than or equal to an over temperature threshold.			
0		b) less than or equal to an under temperature threshold.			
	2	If set to `1', then the NVM subsystem reliability has been degraded due to			
		significant media related errors or any internal error that degrades NVM			
		subsystem reliability.			
	3	If set to '1', then all of the media has been placed in read only mode. The			
		controller shall not set this bit to '1' if the read-only condition on the media			
		is a result of a change in the write protection state of a namespace.			
	4	If set to `1', then the volatile memory backup device has failed. This field is			
		only valid if the controller has a volatile memory backup solution.			
	5	If set to `1', then the Persistent Memory Region has become read-only or			
		unreliable.			
	7:6	Reserved			
	1.1	1			



	Composite Te	Composite Temperature: Contains a value corresponding to a temperature in degrees Kelvin				
	that represents the current composite temperature of the controller and namespace(s)					
	associated with that controller. The manner in which this value is computed is implementation					
1:2	specific and may not represent the actual temperature of any physical point in the NVM					
	subsystem. The	e value of this field may be used to trigger an asynchronous event.				
	Warning and critical overheating composite temperature threshold values are reported by the					
	WCTEMP and C	CTEMP fields in the Identify Controller data structure.				
3	Available Spa	re: Contains a normalized percentage (0 to 100%) of the remaining spare				
3	capacity availal	ole.				
	Available Spa	re Threshold: When the Available Spare falls below the threshold indicated in				
4	this field, an as	ynchronous event completion may occur. The value is indicated as a normalized				
	percentage (0 t	to 100%). The values 101 to 255 are reserved.				
	Percentage Us	sed: Contains a vendor specific estimate of the percentage of NVM subsystem life				
	used based on	the actual usage and the manufacturer's prediction of NVM life. A value of 100				
	indicates that t	he estimated endurance of the NVM in the NVM subsystem has been consumed,				
5	but may not ind	icate an NVM subsystem failure. The value is allowed to exceed 100. Percentages				
	greater than 25	54 shall be represented as 255. This value shall be updated once per power-on				
	hour (when the controller is not in a sleep state).					
	Refer to the JEDEC JESD218A standard for SSD device life and endurance measurement					
	techniques.					
	Endurance Gr	oup Critical Warning Summary: This field indicates critical warnings for the				
	state of Endura	nce Groups. Each bit corresponds to a critical warning type, multiple bits may be				
	set to `1'. If a l	pit is cleared to '0', then that critical warning does not apply to any Endurance				
	Group. Critical	warnings may result in an asynchronous event notification to the host. Bits in this				
	field represent	the current associated state and are not persistent.				
	If a bit is set to	`1' in one or more Endurance Groups, then the corresponding bit shall be set to				
	`1' in this field.					
	Bit	Definition				
6	0	If set to `1', then the available spare capacity of one or more Endurance				
		Groups has fallen below the threshold.				
	1	Reserved				
	2	If set to '1', then the reliability of one or more Endurance Groups has been				
		degraded due to significant media related errors or any internal error that				
		degrades NVM subsystem reliability.				
	3	If set to '1', then the namespaces in one or more Endurance Groups have				
		been placed in read only mode not as a result of a change in the write				
		protection state of a namespace.				
	7:4	Reserved				



7:31	Reserved
32:47	Data Units Read: Contains the number of 512 byte data units the host has read from the controller as part of processing a SMART Data Units Read Command; this value does not include metadata. This value is reported in thousands (i.e., a value of 1 corresponds to 1,000 units of 512 bytes read) and is rounded up (e.g., one indicates that the number of 512 byte data units read is from 1 to 1,000, three indicates that the number of 512 byte data units read is from 2,001 to 3,000). Refer to the specific I/O Command Set specification for the list of SMART Data Units Read Commands that affect this field. A value of 0h in this field indicates that the number of SMART Data Units Read is not reported.
48:63	Data Units Written: Contains the number of 512 byte data units the host has written to the controller as part of processing a User Data Out Command; this value does not include metadata. This value is reported in thousands (i.e., a value of 1 corresponds to 1,000 units of 512 bytes written) and is rounded up (e.g., one indicates that the number of 512 byte data units written is from 1 to 1,000, three indicates that the number of 512 byte data units written is from 2,001 to 3,000). Refer to the specific I/O Command Set specification for the list of User Data Out Commands that affect this field. A value of 0h in this field indicates that the number of Data Units Written is not reported.
64:79	Host Read Commands: Contains the number of SMART Host Read Commands completed by the controller. Refer to the specific I/O Command Set specification for the list of SMART Host Read Commands that affect this field.
80:95	Host Write Commands: Contains the number of User Data Out Commands completed by the controller. Refer to the specific I/O Command Set specification for the list of User Data Out Commands that affect this field.
96:111	Controller Busy Time: Contains the amount of time the controller is busy with I/O commands. The controller is busy when there is a command outstanding to an I/O Queue (specifically, a command was issued via an I/O Submission Queue Tail doorbell write and the corresponding completion queue entry has not been posted yet to the associated I/O Completion Queue). This value is reported in minutes.
112:127	Power Cycles: Contains the number of power cycles.
128:143	Power On Hours: Contains the number of power-on hours. This may not include time that the controller was powered and in a non-operational power state.
144:159	Unsafe Shutdowns: Contains the number of unsafe shutdowns. This count is incremented when the controller does not report it is safe to power down prior to loss of main power.



	Media and Data Integrity Errors: Contains the number of occurrences where the controller
160:175	detected an unrecovered data integrity error. Errors such as uncorrectable ECC, CRC checksum
	failure, or LBA tag mismatch are included in this field. Errors introduced as a result of a Write
	Uncorrectable command (refer to the NVM Command Set Specification) may or may not be
	included in this field.
176:191	Number of Error Information Log Entries: Contains the number of Error Information log
170.191	entries over the life of the controller.
	Warning Composite Temperature Time: Contains the amount of time in minutes that the
	controller is operational and the Composite Temperature is greater than or equal to the Warning
192:195	Composite Temperature Threshold (WCTEMP) field and less than the Critical Composite
192:195	Temperature Threshold (CCTEMP) field in the Identify Controller data structure in Figure 275.
	If the value of the WCTEMP or CCTEMP field is 0h, then this field is always cleared to 0h
	regardless of the Composite Temperature value.
	Critical Composite Temperature Time: Contains the amount of time in minutes that the
	controller is operational and the Composite Temperature is greater than or equal to the Critical
196:199	Composite Temperature Threshold (CCTEMP) field in the Identify Controller data structure.
	If the value of the CCTEMP field is 0h, then this field is always cleared to 0h regardless of the
	Composite Temperature value.
200:201	Temperature Sensor 1: Contains the current temperature reported by the embedded thermal
	sensor in the controller.
202:203	Temperature Sensor 2: Contains the current temperature reported by the embedded thermal
	sensor in the NAND Flash (Channel #0 and CE #0).
204:205	Temperature Sensor 3: Contains the current temperature reported by the embedded thermal
	sensor in the NAND Flash (Channel #0 and CE #0).
206:207	Temperature Sensor 4: Contains the current temperature reported by the embedded thermal
	sensor in the NAND Flash (Last channel and CE #0).
208:209	Temperature Sensor 5: Contains the current temperature reported by temperature sensor 5.
210:211	Temperature Sensor 6: Contains the current temperature reported by temperature sensor 6.
212:213	Temperature Sensor 7: Contains the current temperature reported by temperature sensor 7.
214:215	Temperature Sensor 8: Contains the current temperature reported by temperature sensor 8.
	Thermal Management Temperature 1 Transition Count: Contains the number of times the
216:219	controller transitioned to lower power active power states or performed vendor specific thermal
210.219	management actions while minimizing the impact on performance in order to attempt to reduce
	the Composite Temperature because of the host controlled thermal management feature.
	Thermal Management Temperature 2 Transition Count: Contains the number of times the
	controller transitioned to lower power active power states or performed vendor specific thermal
220:223	management actions regardless of the impact on performance (e.g., heavy throttling) in order
	to attempt to reduce the Composite Temperature because of the host controlled thermal
	management feature.



	Total Time For Thermal Management Temperature 1: Contains the number of seconds that											
	the controller had transitioned to lower power active power states or performed vendor specific											
224:227	thermal management actions while minimizing the impact on performance in order to attempt to											
	reduce the Composite Temperature because of the host controlled thermal management											
	feature.											
	Total Time For Thermal Management Temperature 2: Contains the number of seconds that											
	the controller had transitioned to lower power active power states or performed vendor specific											
228:231	thermal management actions regardless of the impact on performance (e.g., heavy throttling)											
	in order to attempt to reduce the Composite Temperature because of the host controlled thermal											
	management feature.											
232:337	Reserved											
338:345	Later Bad Count											
346:353	Power-On hours Count											
354:361	Drive Power Cycle Count											
362:369	Total Bad Block Count											
370:377	User Max Erase Count											
378:385	User Avg Erase Count											
386:393	Device Life											
394:401	Spare Block Count											
402:409	Program Fail Count											
410:417	Erase Fail Count											
418:425	Unexpected Power Loss Count											
426:433	Temperature (Kelvin - K °K)											
434:441	Flash ID											
442:449	Later Bad Block Info (Read / Write / Erase)											
450:457	Total LBAs Written (unit = 32MB)											
458:465	Total LBAs Read (unit = 32MB)											



6. Part Number Rule

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22			
CODE																									
	D	Н	M	2	8	-	Α	6	0	D	Н	1	K	W	A	Q	L	(W)	(H)	-	X	X			
Def											finition														
Code 1 st (Disk)										Code 14 th (Operation Temperature)															
D : Disk										C: Standard Grade (0°C~ +70°C)															
Code 2 nd (Feature set)									W: Industrial Grade (-40°C∼ +85°C)																
H: iSLC series																									
	Code 3 rd ~5 th (Form factor)												(Code	15 ^t	h (Ir	iteri	nal co	ntrol)						
M28: M.2 Type 2280											A∼Z	: BG	A PC	CB ve	rsio	١.									
			de 7 ^t	th ∼9) th ((Capa	city)							Cł	nann	el o	f data	trans	fer	·)				
	40G: 40GB												D: Dual Channels												
80G: 8											Q: Quad Channels														
A60: 1																									
D2G: 3																									
F4G: 6	40G	В																							
	Code 10 th ~12 th (Controller)											Code 17 th (Flash Type)													
•										L: Innodisk 3D TLC															
	DH2: PCIe 4IE3 series with TCG OPAL function											mou	151(5												
Code 13 th (Flash mode)											Code 18 th ~19 th (Optional Function)														
K: 112 Layers 3D TLC											W: H/W Write Protect Function														
										H: with heatsink accessory (WT default)															
										WH: H/W Write Protect Function + heatsink accessory															
																				_					
										Code 21 st ~ (Customize code)															

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